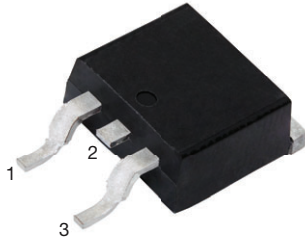
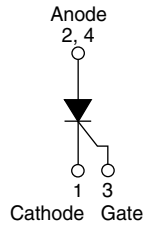


## Thyristor, Surface Mount, Phase Control SCR, 16 A


**D<sup>2</sup>PAK (TO-263AB)**


### FEATURES

- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Designed and qualified according to JEDEC®-JESD 47
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)


**RoHS**  
 COMPLIANT  
 HALOGEN  
**FREE**

### APPLICATIONS

- Input rectification (soft start)
- Vishay input diodes, switches and output rectifiers which are available in identical package outlines

### DESCRIPTION

The VS-25TTS...S-M3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications. The glass passivation technology used has reliable operation up to 125 °C junction temperature.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	16 A
$V_{DRM}/V_{RRM}$	800 V, 1200 V
$V_{TM}$	1.25 V
$I_{GT}$	45 mA
$T_J$	-40 to +125 °C
Package	D <sup>2</sup> PAK (TO-263AB)
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
NEMA FR-4 or G10 glass fabric-based epoxy with 4 oz. (140 µm) copper	3.5	5.5	A
Aluminum IMS, $R_{thCA} = 15$ °C/W	8.5	13.5	
Aluminum IMS with heatsink, $R_{thCA} = 5$ °C/W	16.5	25.0	

#### Note

- $T_A = 55$  °C,  $T_J = 125$  °C, footprint 300 mm<sup>2</sup>

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	16	A
$I_{RMS}$		25	
$V_{RRM}/V_{DRM}$		800 to 1200	V
$I_{TSM}$		350	A
$V_T$	16 A, $T_J = 25$ °C	1.25	V
dV/dt		500	V/µs
dI/dt		150	A/µs
$T_J$		-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	$V_{RRM}$ , MAXIMUM PEAK REVERSE VOLTAGE V	$V_{DRM}$ , MAXIMUM PEAK DIRECT VOLTAGE V	$I_{RRM}/I_{DRM}$ , AT 125 °C mA
VS-25TTS08S-M3	800	800	10
VS-25TTS12S-M3	1200	1200	



ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES		UNITS	
			TYP.	MAX.		
Maximum average on-state current	$I_{T(AV)}$	$T_C = 93\text{ }^\circ\text{C}$ , 180° conduction half sine wave	16		A	
Maximum RMS on-state current	$I_{RMS}$		25			
Maximum peak, one-cycle, non-repetitive surge current	$I_{TSM}$	10 ms sine pulse, rated $V_{RRM}$ applied	300			
		10 ms sine pulse, no voltage reapplied	350			
Maximum $I^2t$ for fusing	$I^2t$	10 ms sine pulse, rated $V_{RRM}$ applied	450		$A^2s$	
		10 ms sine pulse, no voltage reapplied	630			
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	$t = 0.1\text{ ms to }10\text{ ms}$ , no voltage reapplied	6300		$A^2\sqrt{s}$	
Maximum on-state voltage drop	$V_{TM}$	16 A, $T_J = 25\text{ }^\circ\text{C}$	1.25		V	
On-state slope resistance	$r_t$	$T_J = 125\text{ }^\circ\text{C}$	12.0		$m\Omega$	
Threshold voltage	$V_{T(TO)}$		1.0		V	
Maximum reverse and direct leakage current	$I_{RM}/I_{DM}$	$T_J = 25\text{ }^\circ\text{C}$	$V_R = \text{rated } V_{RRM}/V_{DRM}$	0.5		mA
		$T_J = 125\text{ }^\circ\text{C}$		10		
Holding current	$I_H$	VS-25TTS08, VS-25TTS12	Anode supply = 6 V, resistive load, initial $I_T = 1\text{ A}$ , $T_J = 25\text{ }^\circ\text{C}$	-	150	
Maximum latching current	$I_L$	Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$		200		
Maximum rate of rise of off-state voltage	$dV/dt$	$T_J = T_J\text{ max.}$ , linear to 80 %, $V_{DRM} = R_g - k = \text{open}$		500		
Maximum rate of rise of turned-on current	$dI/dt$			150		

TRIGGERING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	$I_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	60	mA
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	45	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	20	
Maximum required DC gate voltage to trigger	$V_{GT}$	Anode supply = 6 V, resistive load, $T_J = -10\text{ }^\circ\text{C}$	2.5	V
		Anode supply = 6 V, resistive load, $T_J = 25\text{ }^\circ\text{C}$	2.0	
		Anode supply = 6 V, resistive load, $T_J = 125\text{ }^\circ\text{C}$	1.0	
Maximum DC gate voltage not to trigger	$V_{GD}$	$T_J = 125\text{ }^\circ\text{C}$ , $V_{DRM} = \text{rated value}$	0.25	
Maximum DC gate current not to trigger	$I_{GD}$		2.0	

SWITCHING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Typical turn-on time	$t_{gt}$	$T_J = 25\text{ }^\circ\text{C}$	0.9	$\mu s$
Typical reverse recovery time	$t_{rr}$	$T_J = 125\text{ }^\circ\text{C}$	4	
Typical turn-off time	$t_q$		110	



THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$		-40 to +125	°C
Maximum thermal resistance, junction to case	$R_{thJC}$	DC operation	1.1	°C/W
Typical thermal resistance, junction to ambient (PCB mount)	$R_{thJA}^{(1)}$		40	
Approximate weight			2	g
			0.07	oz.
Marking device		Case style D <sup>2</sup> PAK (TO-263AB)	25TTS08S	
			25TTS12S	

**Note**

(1) When mounted on 1" square (650 mm<sup>2</sup>) PCB of FR-4 or G-10 material 4 oz. (140 μm) copper 40 °C/W. For recommended footprint and soldering techniques refer to application note #AN-994

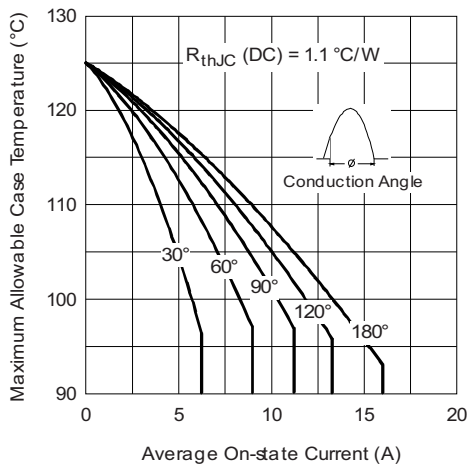


Fig. 1 - Current Rating Characteristics

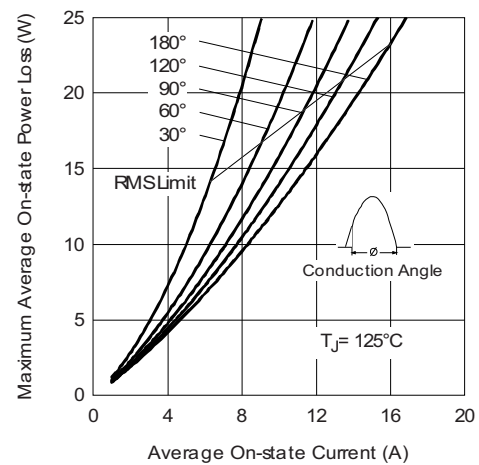


Fig. 3 - On-State Power Loss Characteristics

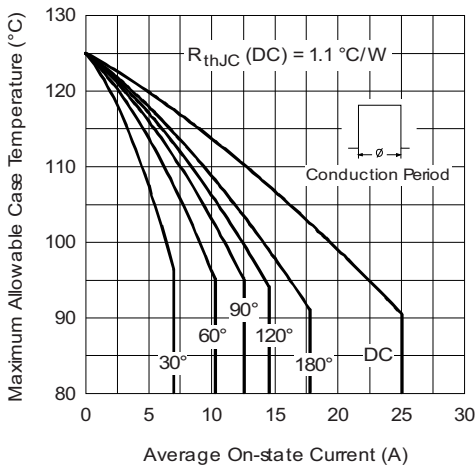


Fig. 2 - Current Rating Characteristics

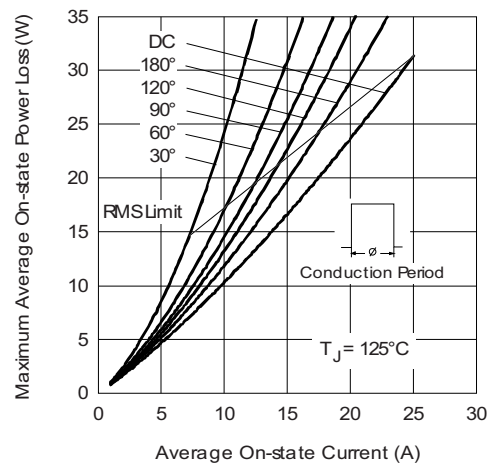


Fig. 4 - On-State Power Loss Characteristics

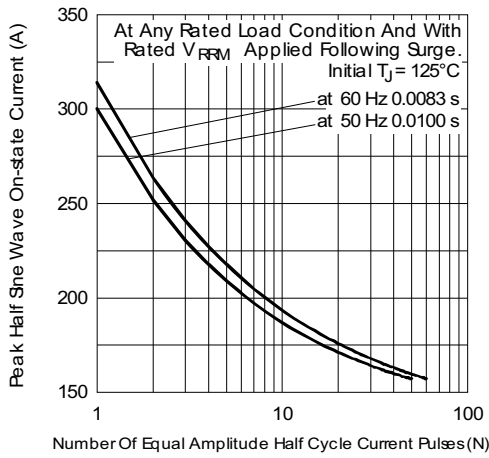


Fig. 5 - Maximum Non-Repetitive Surge Current

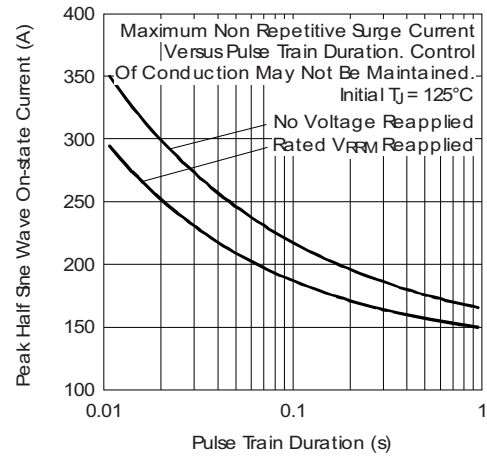


Fig. 6 - Maximum Non-Repetitive Surge Current

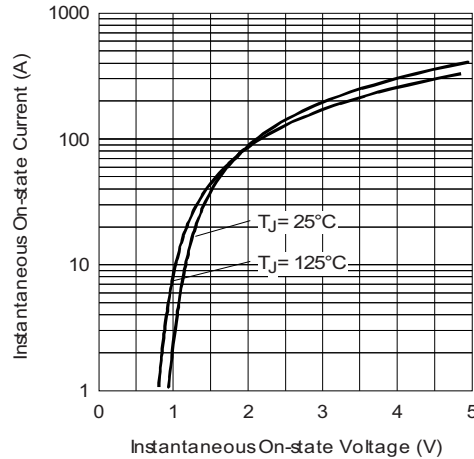


Fig. 7 - On-State Voltage Drop Characteristics

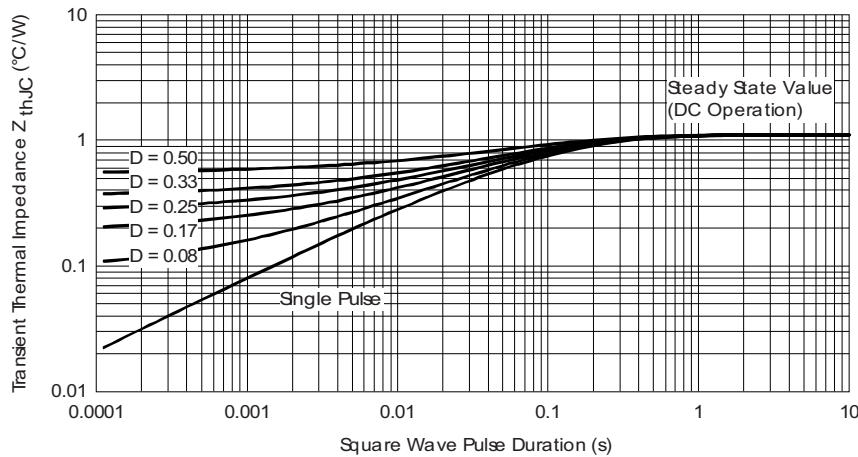


Fig. 8 - Gate Characteristics

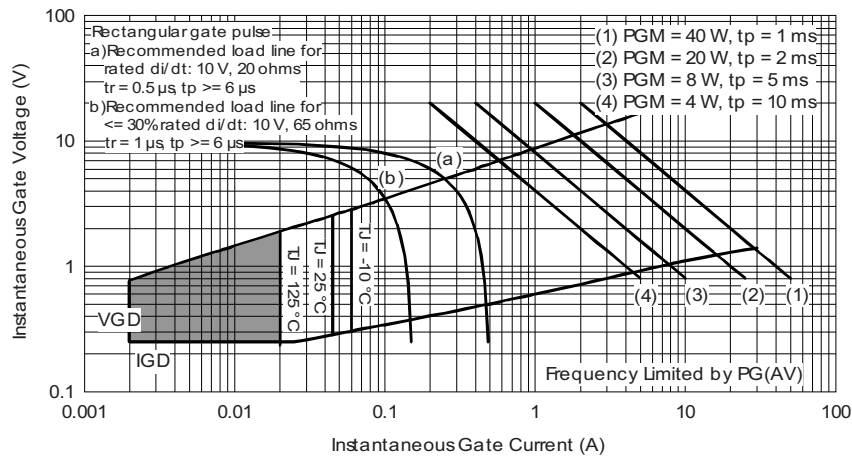


Fig. 9 - Thermal Impedance  $Z_{thJC}$  Characteristics

## ORDERING INFORMATION TABLE

Device code	<b>VS-</b>	<b>25</b>	<b>T</b>	<b>T</b>	<b>S</b>	<b>12</b>	<b>S</b>	<b>TRL</b>	<b>-M3</b>
	(1)	(2)	(3)	(4)	(5)	(6)	(7)	(8)	(9)

- 1** - Vishay Semiconductors product
- 2** - Current rating (25 = 25 A)
- 3** - Circuit configuration:  
T = single thyristor
- 4** - Package:  
T = D<sup>2</sup>PAK (TO-263AB)
- 5** - Type of silicon:  
S = standard recovery rectifier
- 6** - Voltage rating: voltage code x 100 =  $V_{RRM}$
- 7** - S = surface mountable
- 8** -
  - None = tube
  - TRL = tape and reel (left oriented)
  - TRR = tape and reel (right oriented)
- 9** - -M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

08 = 800 V
12 = 1200 V

ORDERING INFORMATION (Example)			
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION
VS-25TTS08S-M3	50	1000	Antistatic plastic tubes
VS-25TTS08STRR-M3	800	800	13" diameter reel
VS-25TTS08STRL-M3	800	800	13" diameter reel
VS-25TTS12S-M3	50	1000	Antistatic plastic tubes
VS-25TTS12STRR-M3	800	800	13" diameter reel
VS-25TTS12STRL-M3	800	800	13" diameter reel

LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?96164">www.vishay.com/doc?96164</a>
Part marking information	<a href="http://www.vishay.com/doc?95444">www.vishay.com/doc?95444</a>
Packaging information	<a href="http://www.vishay.com/doc?96424">www.vishay.com/doc?96424</a>

### D<sup>2</sup>PAK

**DIMENSIONS** in millimeters and inches

Conforms to JEDEC<sup>®</sup> outline D<sup>2</sup>PAK (SMD-220)



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.			MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	0.160	0.190		D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010		E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039		E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4	e	2.54 BSC		0.100 BSC		
b2	1.14	1.78	0.045	0.070		H	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4	L	1.78	2.79	0.070	0.110	
c	0.38	0.74	0.015	0.029		L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4	L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065		L3	0.25 BSC		0.010 BSC		
D	8.51	9.65	0.335	0.380	2	L4	4.78	5.28	0.188	0.208	

**Notes**

- (1) Dimensioning and tolerancing per ASME Y14.5 M-1994
- (2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
- (3) Thermal pad contour optional within dimension E, L1, D1 and E1
- (4) Dimension b1 and c1 apply to base metal only
- (5) Datum A and B to be determined at datum plane H
- (6) Controlling dimension: inches
- (7) Outline conforms to JEDEC<sup>®</sup> outline TO-263AB



## **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.